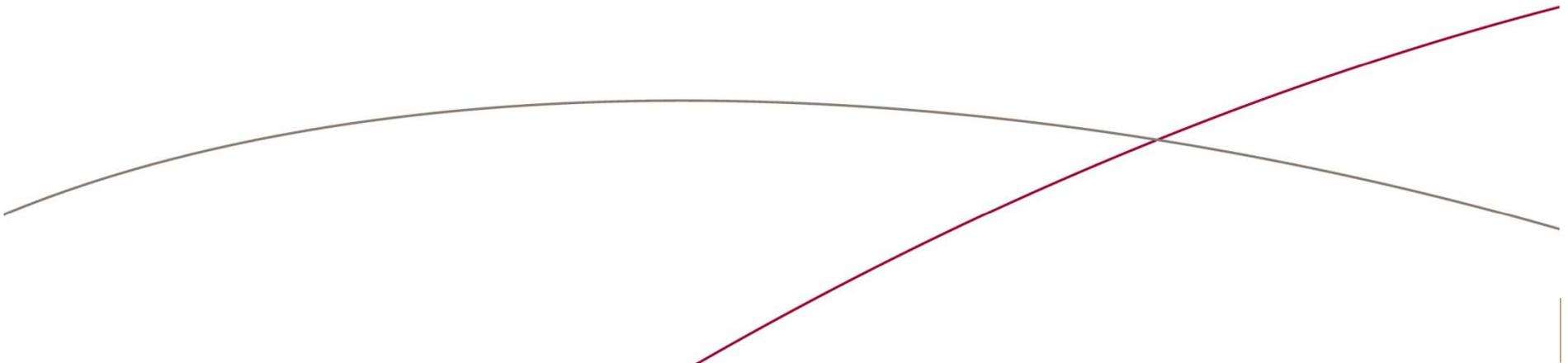


2010/11 – Advances in RF and mixed-signal cellular IC design

Mattias Andersson, Jonas Lindstrand, Martin Liliebladh, Ping Lu, Daniele Mastantuono, Luca Fanori, Martin Anderson, Lars Sundström, Pietro Andreani

Department for Electrical and Information Technology
Lund University



Overview

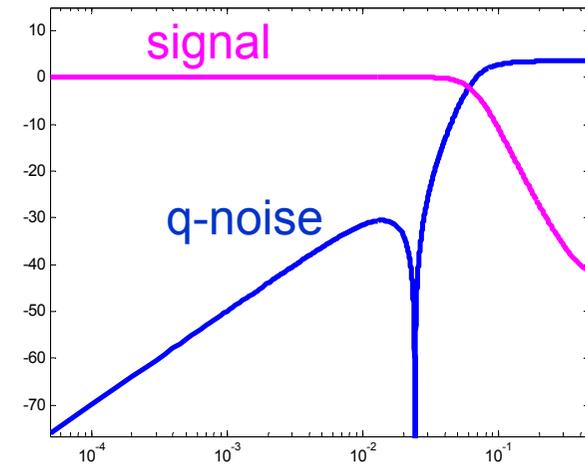
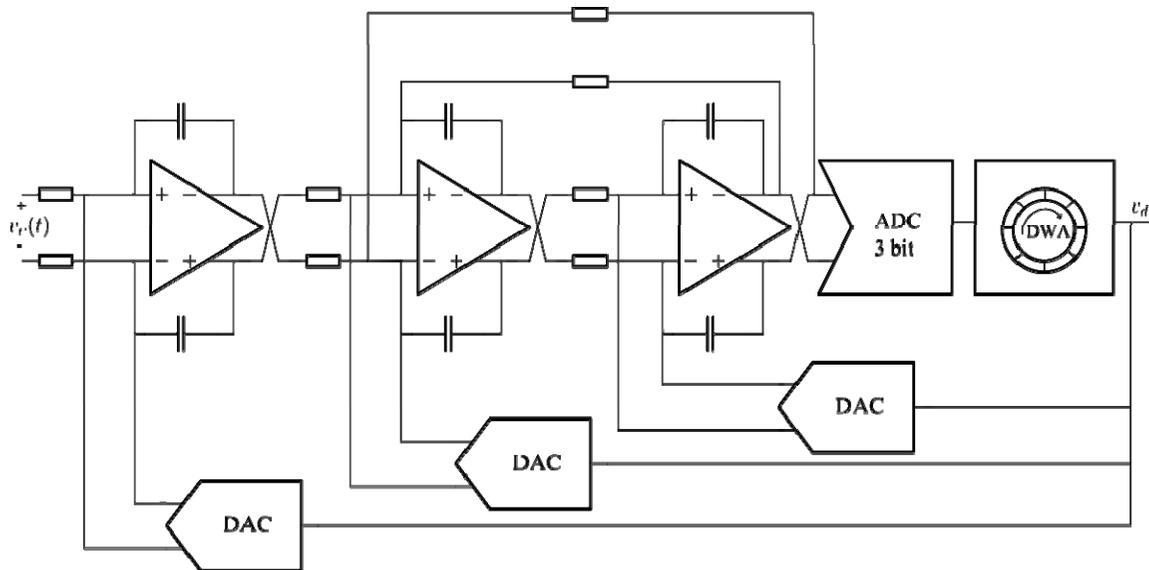
- An beautiful continuous-time $\Delta\Sigma$ A/D converter
 - **Mattias Andersson**
- An impressive 30dBm power amplifier
 - **Jonas Lindstrand**
- An amazing time-to-digital converter
 - **Ping Lu**



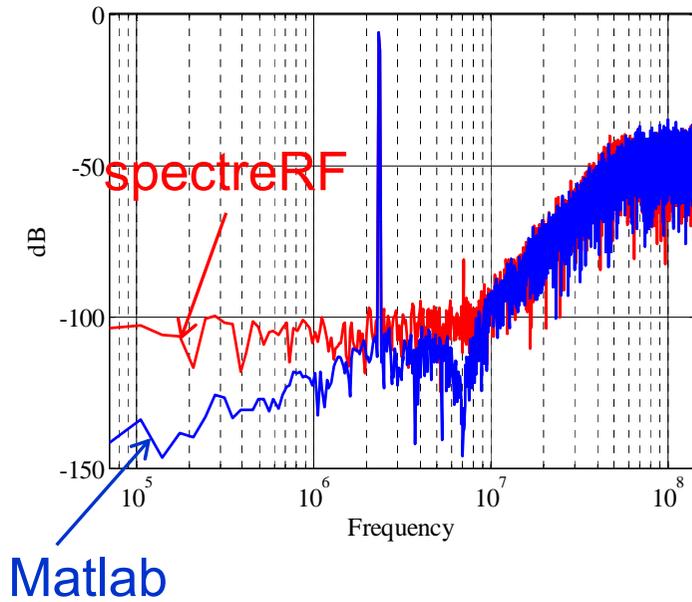
Continuous-Time $\Delta\Sigma$ ADC for LTE

- 3rd order, 3-bit, $f_s=288\text{MHz}$, $\text{BW}=9\text{MHz}$ ($\text{OSR}=16$)

Mattias Andersson



Simulation results



65nm CMOS



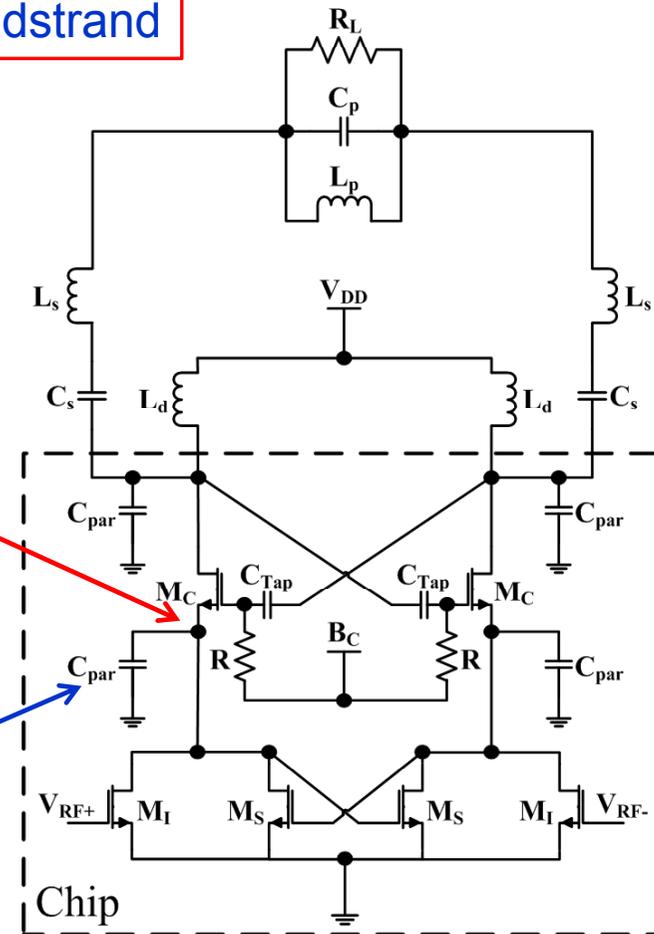
Very good predictions
with spectreRF +
transient noise



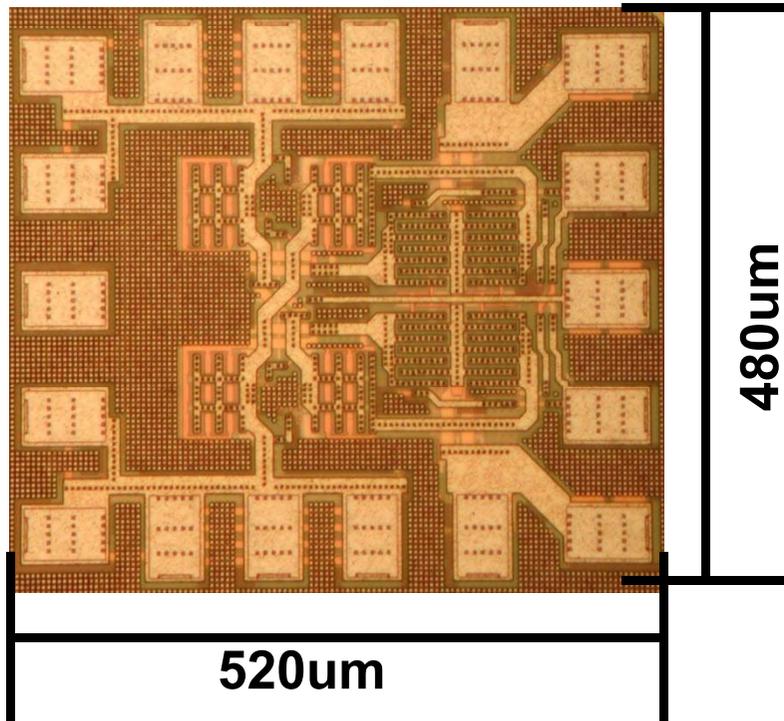
Power Amplifier in 65nm CMOS

Jonas Lindstrand

- Self-oscillating PA
 - Supply (V_{dd}) modulation
 - Reduced switching losses
- Wideband injection lock
 - Resistive injection node
 - M_S amplifies injected current
- Tapped cascode
 - $C_{Tap} + C_{par,Mc}$
 - Reduced stress on M_I/M_S
 - Reduced “SC” loss on C_{par}



Chip photograph

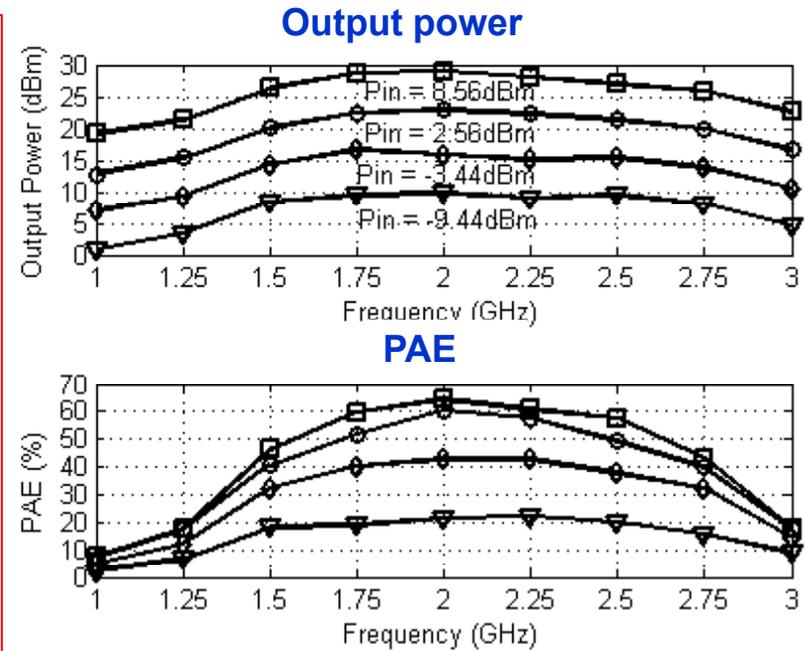
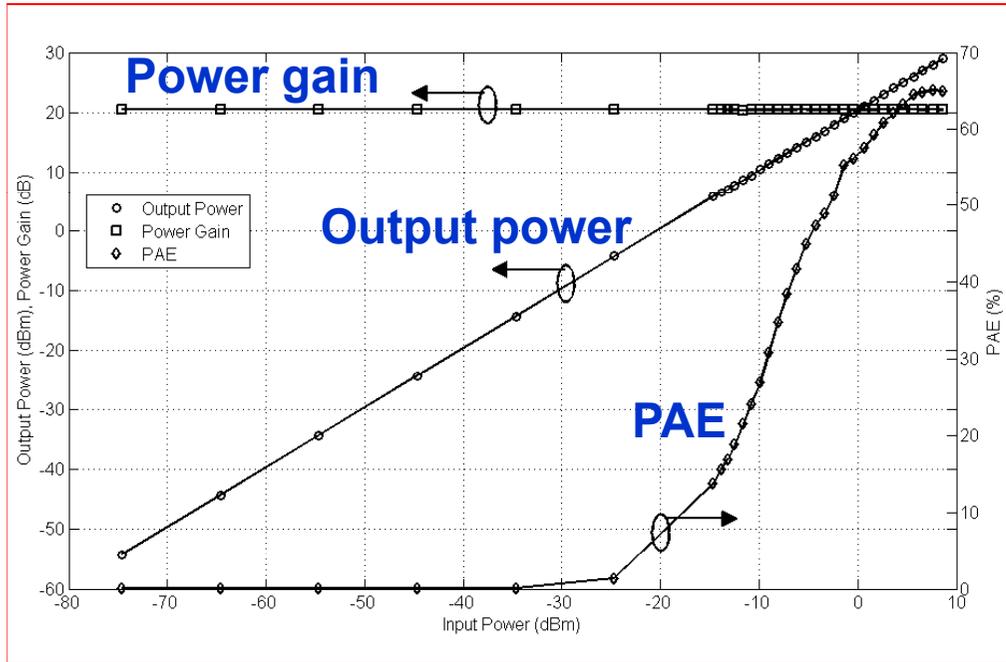


Presented at ESSCIRC 2011

**Highest ranked paper
in the RF sub-committee!**



Measurement results



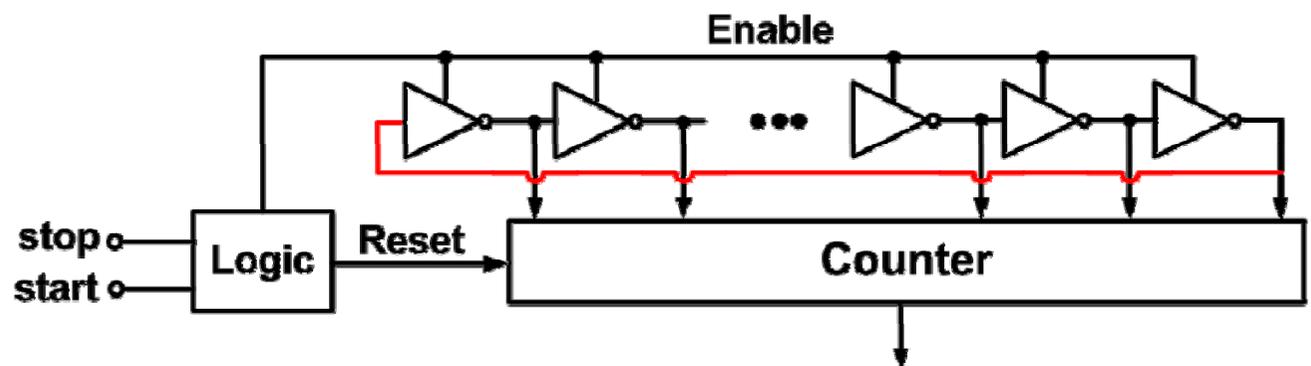
STATE OF THE ART!



Time-to-digital converter (TDC)

Ping Lu

- Smaller TDC-cell delay (Δt_{delay}) \rightarrow lower in-band PLL noise
- Vernier TDC $\rightarrow \tau_1 - \tau_2 = \Delta t_{\text{delay}} < \tau_1$ (τ_2)
 - However, a very large number of stages are required
- Ring-Oscillator (RO) TDC \rightarrow large detection range with few stages
 - ✓ Gated-RO TDC \rightarrow quantization noise pushed to high frequencies



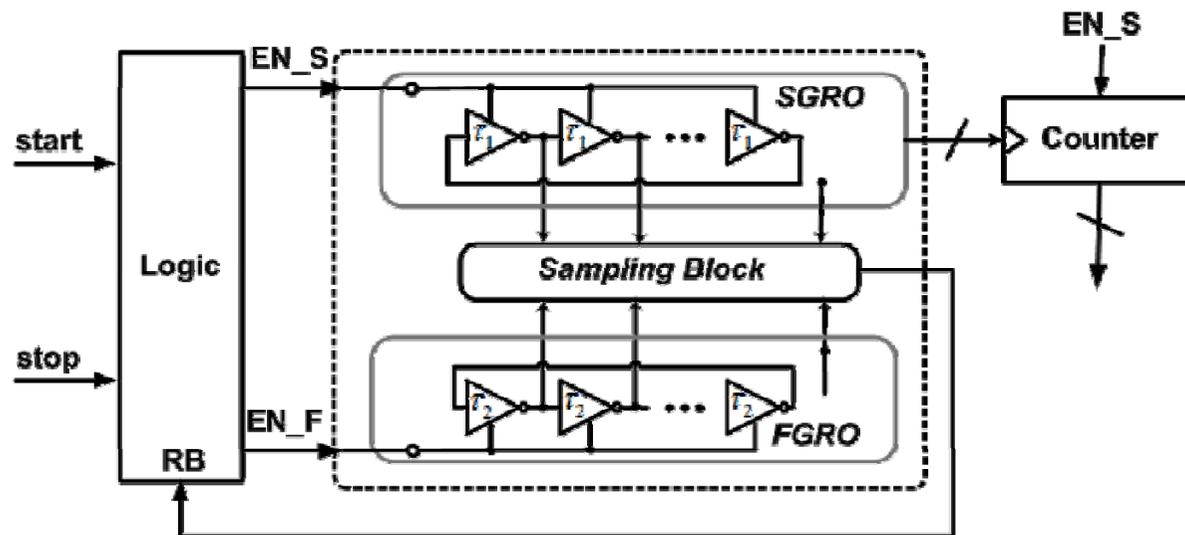
Gated-Ring-Oscillator TDC

(B.M. Helal, et al. JSSC, Apr. 2008)

However, coarse resolution still limited by an inverter delay

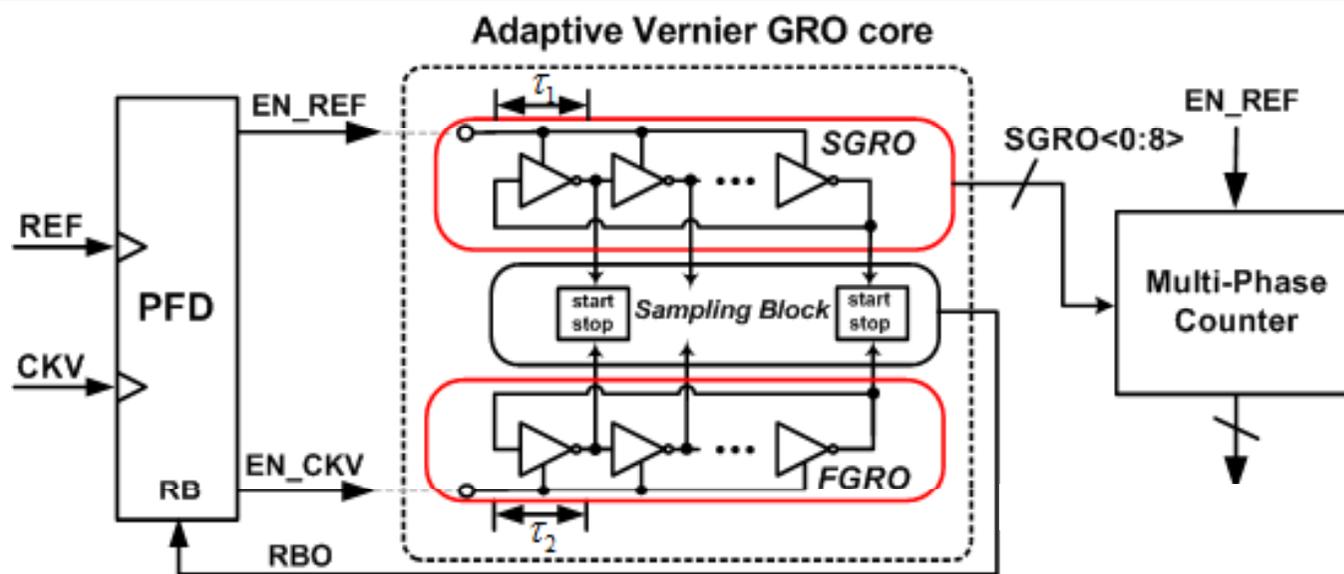
Vernier + gated ring oscillator

- New TDC → combines Vernier + GRO

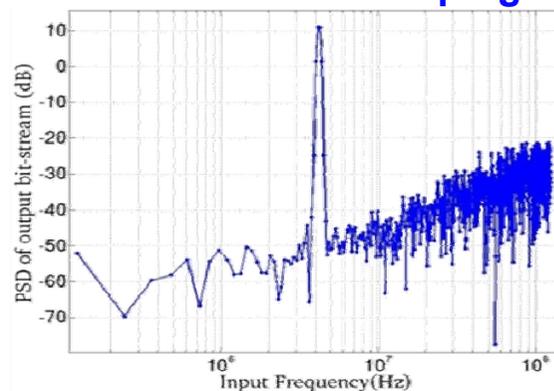


High Vernier time resolution + First-order noise shaping

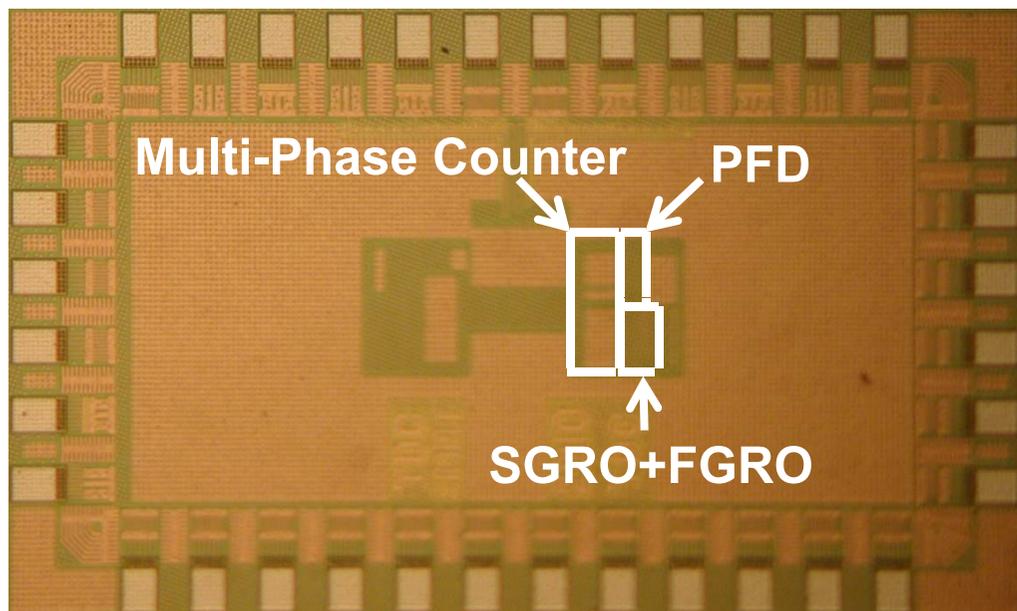
Noise shaping



1st-order noise shaping



Chip photograph



Presented at ESSCIRC 2011

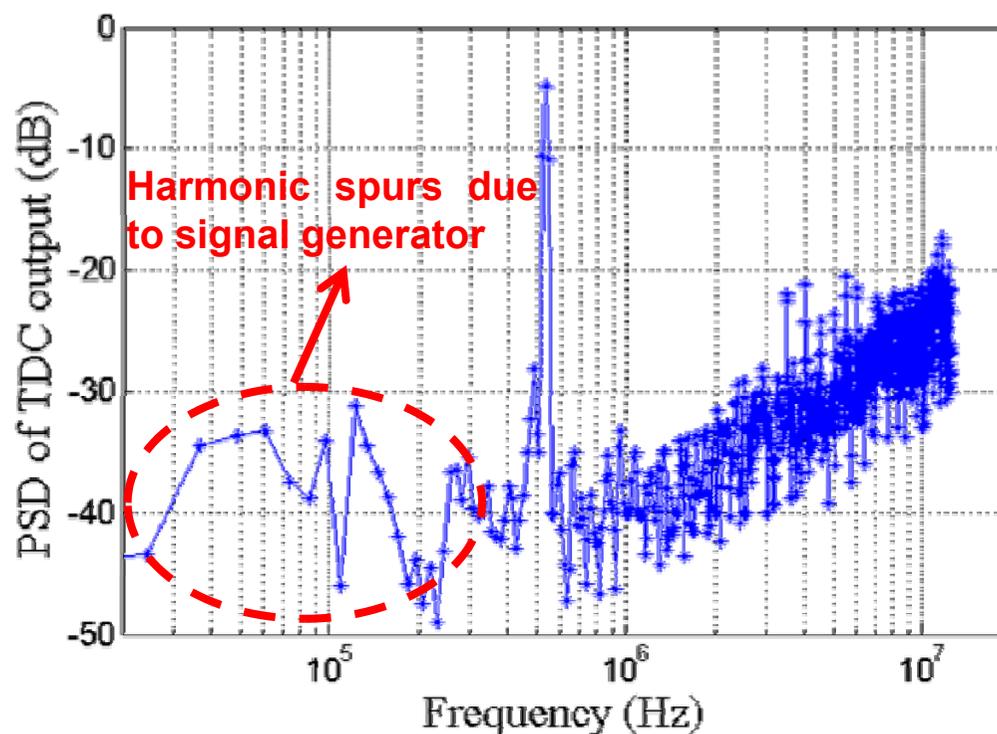
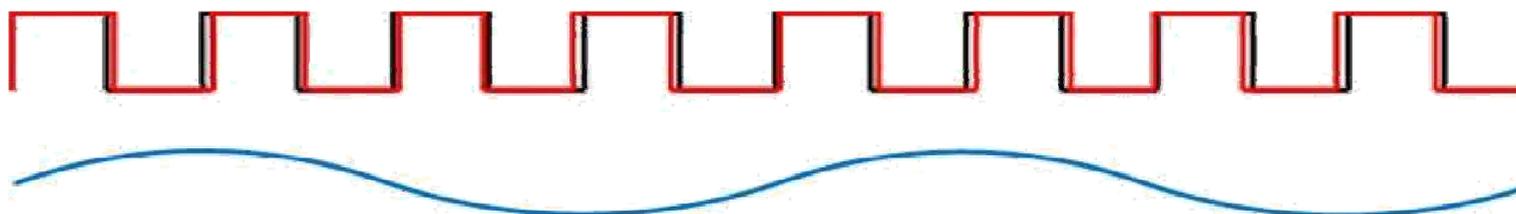
**3rd highest ranked paper
in the RF sub-committee!
(only 0.03 from top!)**



Area	0.027mm²
Process	90nm CMOS
Current (Supply)	3mA (1.2V)
Vernier resolution	~5ps
Effective in-band resolution (OSR= 16)	~3ps



Measurement results – sinusoidal input



TDC output PSD with sinusoidal delay input (500KHz)





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